

# Tadeusz Suski

## List of Publications by Citations

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305  
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80  
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344  
ext. papers

8,707  
ext. citations

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L-index

#	Paper	IF	Citations
305	Strain-related phenomena in GaN thin films. <i>Physical Review B</i> , <b>1996</b> , 54, 17745-17753	3.3	719
304	Observation of Native Ga Vacancies in GaN by Positron Annihilation. <i>Physical Review Letters</i> , <b>1997</b> , 79, 3030-3033	7.4	411
303	Lattice parameters of gallium nitride. <i>Applied Physics Letters</i> , <b>1996</b> , 69, 73-75	3.4	325
302	Towards the identification of the dominant donor in GaN. <i>Physical Review Letters</i> , <b>1995</b> , 75, 296-299	7.4	266
301	Large, nitrogen-induced increase of the electron effective mass in InyGa1-yNxAs1-x. <i>Applied Physics Letters</i> , <b>2000</b> , 76, 2409-2411	3.4	212
300	Pressure Induced Deep Gap State of Oxygen in GaN. <i>Physical Review Letters</i> , <b>1997</b> , 78, 3923-3926	7.4	208
299	Mechanism of yellow luminescence in GaN. <i>Applied Physics Letters</i> , <b>1995</b> , 67, 2188-2190	3.4	193
298	Investigation of longitudinal-optical phonon-plasmon coupled modes in highly conducting bulk GaN. <i>Applied Physics Letters</i> , <b>1995</b> , 67, 2524-2526	3.4	192
297	Thermal expansion of gallium nitride. <i>Journal of Applied Physics</i> , <b>1994</b> , 76, 4909-4911	2.5	179
296	Phonon dispersion curves in wurtzite-structure GaN determined by inelastic x-ray scattering. <i>Physical Review Letters</i> , <b>2001</b> , 86, 906-9	7.4	158
295	Temperature dependence of the energy gap in GaN bulk single crystals and epitaxial layer. <i>Journal of Applied Physics</i> , <b>1994</b> , 76, 2429-2434	2.5	155
294	Effect of Si doping on the dislocation structure of GaN grown on the A-face of sapphire. <i>Applied Physics Letters</i> , <b>1996</b> , 69, 990-992	3.4	151
293	Pressure studies of gallium nitride: Crystal growth and fundamental electronic properties. <i>Physical Review B</i> , <b>1992</b> , 45, 13307-13313	3.3	138
292	Thermal conductivity of GaN crystals in 4.2-300 K range. <i>Solid State Communications</i> , <b>2003</b> , 128, 69-73	1.6	127
291	Determination of the effective mass of GaN from infrared reflectivity and Hall effect. <i>Applied Physics Letters</i> , <b>1996</b> , 68, 1114-1116	3.4	124
290	Influence of indium clustering on the band structure of semiconducting ternary and quaternary nitride alloys. <i>Physical Review B</i> , <b>2009</b> , 80,	3.3	123
289	Thermal stability of isolated and complexed Ga vacancies in GaN bulk crystals. <i>Physical Review B</i> , <b>2001</b> , 64,	3.3	117

288	High electron mobility in AlGa <sub>N</sub> /Ga <sub>N</sub> heterostructures grown on bulk Ga <sub>N</sub> substrates. <i>Applied Physics Letters</i> , <b>2000</b> , 77, 2551-2553	3-4	103
287	Influence of dopants and substrate material on the formation of Ga vacancies in epitaxial Ga <sub>N</sub> layers. <i>Physical Review B</i> , <b>2001</b> , 63,	3-3	92
286	Influence of pressure on photoluminescence and electroluminescence in Ga <sub>N</sub> /InGa <sub>N</sub> /AlGa <sub>N</sub> quantum wells. <i>Applied Physics Letters</i> , <b>1997</b> , 70, 2993-2995	3-4	83
285	Effect of growth polarity on vacancy defect and impurity incorporation in dislocation-free Ga <sub>N</sub> . <i>Applied Physics Letters</i> , <b>2005</b> , 86, 031915	3-4	80
284	The influence of Mg doping on the formation of Ga vacancies and negative ions in Ga <sub>N</sub> bulk crystals. <i>Applied Physics Letters</i> , <b>1999</b> , 75, 2441-2443	3-4	69
283	Interdiffusion of In and Ga in InGa <sub>N</sub> quantum wells. <i>Applied Physics Letters</i> , <b>1998</b> , 73, 1281-1283	3-4	66
282	Heat capacity of Ga <sub>N</sub> : Isotope effects. <i>Physical Review B</i> , <b>2005</b> , 72,	3-3	65
281	Degradation mechanisms in InGa <sub>N</sub> laser diodes grown on bulk Ga <sub>N</sub> crystals. <i>Applied Physics Letters</i> , <b>2006</b> , 88, 201111	3-4	64
280	Piezoelectric field and its influence on the pressure behavior of the light emission from Ga <sub>N</sub> /AlGa <sub>N</sub> strained quantum wells. <i>Applied Physics Letters</i> , <b>2001</b> , 79, 1483-1485	3-4	64
279	Blue-violet InGa <sub>N</sub> laser diodes grown on bulk Ga <sub>N</sub> substrates by plasma-assisted molecular-beam epitaxy. <i>Applied Physics Letters</i> , <b>2005</b> , 86, 011114	3-4	62
278	Interband optical absorption in free standing layer of Ga <sub>0.96</sub> In <sub>0.04</sub> As <sub>0.99</sub> N <sub>0.01</sub> . <i>Applied Physics Letters</i> , <b>2000</b> , 76, 1279-1281	3-4	62
277	Influence of pressure on the optical properties of In <sub>x</sub> Ga <sub>1-x</sub> N epilayers and quantum structures. <i>Physical Review B</i> , <b>2001</b> , 64,	3-3	61
276	Highly reproducible, stable and multiply regenerated surface-enhanced Raman scattering substrate for biomedical applications. <i>Journal of Materials Chemistry</i> , <b>2011</b> , 21, 8662		59
275	Band structure and optical properties of In <sub>y</sub> Ga <sub>1-y</sub> As <sub>1-x</sub> N <sub>x</sub> alloys. <i>Physical Review B</i> , <b>2001</b> , 65,	3-3	58
274	Lattice constants, thermal expansion and compressibility of gallium nitride. <i>Journal Physics D: Applied Physics</i> , <b>1995</b> , 28, A149-A153	3	58
273	High mobility two-dimensional electron gas in AlGa <sub>N</sub> /Ga <sub>N</sub> heterostructures grown on bulk Ga <sub>N</sub> by plasma assisted molecular beam epitaxy. <i>Applied Physics Letters</i> , <b>2005</b> , 86, 102106	3-4	52
272	Evidence for localized Si-donor state and its metastable properties in AlGa <sub>N</sub> . <i>Applied Physics Letters</i> , <b>1999</b> , 74, 3833-3835	3-4	50
271	Bowing of the band gap pressure coefficient in In <sub>x</sub> Ga <sub>1-x</sub> N alloys. <i>Journal of Applied Physics</i> , <b>2008</b> , 103, 033514	2-5	48

270	The microstructure of gallium nitride monocrystals grown at high pressure. <i>Journal of Crystal Growth</i> , <b>1996</b> , 169, 235-242	1.6	47
269	Infrared spectroscopy of Mg-H local vibrational mode in GaN with polarized light. <i>Physical Review B</i> , <b>2000</b> , 61, 8238-8241	3.3	46
268	Role of the electron blocking layer in the low-temperature collapse of electroluminescence in nitride light-emitting diodes. <i>Applied Physics Letters</i> , <b>2007</b> , 90, 103507	3.4	44
267	Temperature dependence of electrical properties of gallium-nitride bulk single crystals doped with Mg and their evolution with annealing. <i>Journal of Applied Physics</i> , <b>2001</b> , 89, 7960-7965	2.5	43
266	Photocurrent spectroscopy as a tool for determining piezoelectric fields in In <sub>x</sub> Ga <sub>1-x</sub> N/GaN multiple quantum well light emitting diodes. <i>Physical Review B</i> , <b>2004</b> , 69,	3.3	42
265	The discrepancies between theory and experiment in the optical emission of monolayer In(Ga)N quantum wells revisited by transmission electron microscopy. <i>Applied Physics Letters</i> , <b>2014</b> , 104, 182103	3.4	41
264	Decay of stimulated and spontaneous emission in highly excited homoepitaxial GaN. <i>Applied Physics Letters</i> , <b>2001</b> , 78, 3776-3778	3.4	41
263	Optically pumped 500 nm InGaN green lasers grown by plasma-assisted molecular beam epitaxy. <i>Journal of Applied Physics</i> , <b>2011</b> , 110, 063110	2.5	39
262	High pressure and DX centers in heavily doped bulk GaAs. <i>Physical Review B</i> , <b>1989</b> , 40, 4012-4021	3.3	39
261	X-ray absorption, glancing-angle reflectivity, and theoretical study of the N K- and Ga M <sub>2,3</sub> -edge spectra in GaN. <i>Physical Review B</i> , <b>1997</b> , 55, 2612-2622	3.3	38
260	Doping of Homoepitaxial GaN Layers. <i>Physica Status Solidi (B): Basic Research</i> , <b>1998</b> , 210, 437-443	1.3	38
259	Limitations to band gap tuning in nitride semiconductor alloys. <i>Applied Physics Letters</i> , <b>2010</b> , 96, 101907	3.4	37
258	Fully-screened polarization-induced electric fields in blue-violet InGaN/GaN light-emitting devices grown on bulk GaN. <i>Applied Physics Letters</i> , <b>2005</b> , 87, 041109	3.4	37
257	Band Structure and Quantum Confined Stark Effect in InN/GaN superlattices. <i>Crystal Growth and Design</i> , <b>2012</b> , 12, 3521-3525	3.5	36
256	Phase separation in InGaN multiple quantum wells annealed at high nitrogen pressures. <i>Applied Physics Letters</i> , <b>1999</b> , 75, 3950-3952	3.4	36
255	Correlation between luminescence and compositional striations in InGaN layers grown on miscut GaN substrates. <i>Applied Physics Letters</i> , <b>2007</b> , 91, 211904	3.4	35
254	Structural Defects in Heteroepitaxial and Homoepitaxial GaN. <i>Materials Research Society Symposia Proceedings</i> , <b>1995</b> , 395, 351		34
253	GaN homoepitaxial layers grown by metalorganic chemical vapor deposition. <i>Applied Physics Letters</i> , <b>1999</b> , 75, 1276-1278	3.4	33

252	Indium incorporation into InGaN and InAlN layers grown by metalorganic vapor phase epitaxy. <i>Journal of Crystal Growth</i> , <b>2011</b> , 318, 496-499	1.6	32
251	Different character of the donor-acceptor pair-related 3.27 eV band and blue photoluminescence in Mg-doped GaN. Hydrostatic pressure studies. <i>Physical Review B</i> , <b>2000</b> , 62, 10151-10157	3.3	31
250	High power blue-violet InGaN laser diodes grown on bulk GaN substrates by plasma-assisted molecular beam epitaxy. <i>Semiconductor Science and Technology</i> , <b>2005</b> , 20, 809-813	1.8	30
249	Optical and electrical properties of homoepitaxially grown multiquantum well InGaN/GaN light-emitting diodes. <i>Journal of Applied Physics</i> , <b>2003</b> , 94, 6122-6128	2.5	30
248	High-pressure high-temperature annealing of ion-implanted GaN films monitored by visible and ultraviolet micro-Raman scattering. <i>Journal of Applied Physics</i> , <b>2000</b> , 87, 2736-2741	2.5	30
247	Homoepitaxial growth of GaN using molecular beam epitaxy. <i>Journal of Applied Physics</i> , <b>1996</b> , 80, 2195-2198	1.98	30
246	Influence of GaN substrate off-cut on properties of InGaN and AlGaIn layers. <i>Crystal Research and Technology</i> , <b>2012</b> , 47, 321-328	1.3	28
245	Evidence of free carrier concentration gradient along the c-axis for undoped GaN single crystals. <i>Journal of Crystal Growth</i> , <b>2001</b> , 230, 442-447	1.6	28
244	Picosecond Z-scan measurements on bulk GaN crystals. <i>Applied Physics Letters</i> , <b>2001</b> , 78, 4118-4120	3.4	28
243	Size effects in band gap bowing in nitride semiconducting alloys. <i>Physical Review B</i> , <b>2011</b> , 83,	3.3	27
242	Cavity suppression in nitride based superluminescent diodes. <i>Journal of Applied Physics</i> , <b>2012</b> , 111, 083106	1.6	27
241	Role of conduction-band filling in the dependence of InN photoluminescence on hydrostatic pressure. <i>Physical Review B</i> , <b>2007</b> , 76,	3.3	27
240	Effect of high-temperature annealing on the residual strain and bending of freestanding GaN films grown by hydride vapor phase epitaxy. <i>Applied Physics Letters</i> , <b>2006</b> , 88, 141909	3.4	27
239	A pressure-tuned blue-violet InGaN/GaN laser diode grown on bulk GaN crystal. <i>Applied Physics Letters</i> , <b>2004</b> , 84, 1236-1238	3.4	27
238	Thermal conductivity of GaN crystals grown by high pressure method. <i>Physica Status Solidi (B): Basic Research</i> , <b>2003</b> , 240, 447-450	1.3	27
237	High-nitrogen-pressure growth of GaN single crystals: doping and physical properties. <i>Journal of Physics Condensed Matter</i> , <b>2001</b> , 13, 8881-8890	1.8	27
236	Band gap bowing in quaternary nitride semiconducting alloys. <i>Applied Physics Letters</i> , <b>2011</b> , 98, 241905	3.4	26
235	Anomalous composition dependence of the band gap pressure coefficients in In-containing nitride semiconductors. <i>Physical Review B</i> , <b>2010</b> , 81,	3.3	26

- 234 Intrinsic dynamics of weakly and strongly confined excitons in nonpolar nitride-based heterostructures. *Physical Review B*, **2011**, 83, 3-3 26
- 233 Substrate misorientation induced strong increase in the hole concentration in Mg doped GaN grown by metalorganic vapor phase epitaxy. *Applied Physics Letters*, **2008**, 93, 172117 3-4 26
- 232 Annealing of GaN under high pressure of nitrogen. *Journal of Physics Condensed Matter*, **2002**, 14, 110971-111026 1-8 26
- 231 Photoluminescence and pressure effects in short period InN/nGaN superlattices. *Journal of Applied Physics*, **2013**, 113, 123101 2-5 25
- 230 Search for free holes in InN:Mg-interplay between surface layer and Mg-acceptor doped interior. *Journal of Applied Physics*, **2009**, 105, 123713 2-5 25
- 229 Electronic structure and effective masses of InN under pressure. *Journal of Applied Physics*, **2008**, 104, 013704 2-5 25
- 228 Free and bound excitons in GaN/AlGaN homoepitaxial quantum wells grown on bulk GaN substrate along the nonpolar (1120) direction. *Applied Physics Letters*, **2005**, 86, 162112 3-4 25
- 227 Factor group analysis of the Raman spectrum of Pb5Ge3O11. *Physica Status Solidi (B): Basic Research*, **1977**, 80, 31-41 1-3 25
- 226 Thermal conductivity of heavily doped bulk crystals GaN:O. Free carriers contribution. *Materials Research Express*, **2015**, 2, 085902 1-7 24
- 225 Graded-index separate confinement heterostructure InGaN laser diodes. *Applied Physics Letters*, **2013**, 103, 261107 3-4 24
- 224 Vacancies as compensating centers in bulk GaN: doping effects. *Journal of Crystal Growth*, **2002**, 246, 281-286 1-6 24
- 223 Ga vacancies in electron irradiated GaN: introduction, stability and temperature dependence of positron trapping. *Physica B: Condensed Matter*, **2001**, 308-310, 77-80 2-8 23
- 222 Hydrostatic pressure and strain effects in short period InN/GaN superlattices. *Applied Physics Letters*, **2012**, 101, 092104 3-4 22
- 221 GaN Crystals: Growth and Doping Under Pressure. *Materials Research Society Symposia Proceedings*, **1997**, 482, 115 22
- 220 Lateral Control of Indium Content and Wavelength of III-Nitride Diode Lasers by Means of GaN Substrate Patterning. *Applied Physics Express*, **2012**, 5, 021001 2-4 21
- 219 Determination of built-in electric fields in quaternary InAlGaIn heterostructures. *Applied Physics Letters*, **2003**, 82, 1541-1543 3-4 21
- 218 Pressure and composition dependence of the electronic structure of GaAs<sub>1-x</sub>N<sub>x</sub>. *Physical Review B*, **2002**, 66, 3-3 21
- 217 The Application of High Pressure in Physics and Technology of III-V Nitrides. *Acta Physica Polonica A*, **2001**, 100, 57-109 0-6 21

216	Theoretical study of nitride short period superlattices. <i>Journal of Physics Condensed Matter</i> , <b>2018</b> , 30, 063001	1.8	20
215	Theoretical study of the composition pulling effect in InGaN metalorganic vapor-phase epitaxy growth. <i>Japanese Journal of Applied Physics</i> , <b>2017</b> , 56, 078003	1.4	20
214	Effect of hydrogen during growth of quantum barriers on the properties of InGaN quantum wells. <i>Journal of Crystal Growth</i> , <b>2015</b> , 414, 38-41	1.6	20
213	Polarity dependent properties of GaN layers grown by hydride vapor phase epitaxy on GaN bulk crystals. <i>Physica Status Solidi (B): Basic Research</i> , <b>2003</b> , 240, 289-292	1.3	20
212	Efficient radiative recombination and potential profile fluctuations in low-dislocation InGaN/GaN multiple quantum wells on bulk GaN substrates. <i>Journal of Applied Physics</i> , <b>2005</b> , 97, 103507	2.5	20
211	Observation of Ga vacancies and negative ions in undoped and Mg-doped GaN bulk crystals. <i>Physica B: Condensed Matter</i> , <b>1999</b> , 273-274, 33-38	2.8	20
210	Lattice parameters of GaN single crystals, homoepitaxial layers and heteroepitaxial layers on sapphire. <i>Journal of Alloys and Compounds</i> , <b>1999</b> , 286, 271-275	5.7	20
209	Revealing of the transition from n- to p-type conduction of InN:Mg by photoconductivity effect measurement. <i>Scientific Reports</i> , <b>2014</b> , 4, 4371	4.9	19
208	Effect of efficiency droop in violet and blue InGaN laser diodes. <i>Applied Physics Letters</i> , <b>2009</b> , 95, 071108	3.4	19
207	Different pressure behavior of GaN/AlGaIn quantum structures grown along polar and nonpolar crystallographic directions. <i>Journal of Applied Physics</i> , <b>2009</b> , 105, 063104	2.5	19
206	Built-in electric field and large Stokes shift in near-lattice-matched GaN/AlInN quantum wells. <i>Applied Physics Letters</i> , <b>2008</b> , 92, 201901	3.4	19
205	Anomalous temperature characteristics of single wide quantum well InGaIn laser diode. <i>Applied Physics Letters</i> , <b>2006</b> , 88, 071121	3.4	19
204	Growth of AlN, GaN and InN from the solution. <i>International Journal of Materials and Product Technology</i> , <b>2005</b> , 22, 226	1	19
203	Spatial distribution of electron concentration and strain in bulk GaN single crystals - relation to growth mechanism. <i>Materials Research Society Symposia Proceedings</i> , <b>1996</b> , 449, 519		19
202	New phenomena of low temperature resistivity enhancement in quantum ferroelectric semiconductors. <i>Solid State Communications</i> , <b>1983</b> , 45, 259-262	1.6	19
201	Stimulated emission due to spatially separated electron-hole plasma and exciton system in homoepitaxial GaN. <i>Physical Review B</i> , <b>2004</b> , 69,	3.3	18
200	Effective mass and conduction band dispersion of GaAsN/GaAs quantum wells. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , <b>2002</b> , 13, 1078-1081	3	18
199	Time-resolved spectroscopy of (Al,Ga,In)N based quantum wells: Localization effects and effective reduction of internal electric fields. <i>Physical Review B</i> , <b>2002</b> , 66,	3.3	18

198	Influence of internal electric fields on band gaps in short period GaN/GaAlN and InGaN/GaN polar superlattices. <i>Journal of Applied Physics</i> , <b>2015</b> , 118, 075702	2.5	17
197	Temperature dependence of superluminescence in InGaN-based superluminescent light emitting diode structures. <i>Journal of Applied Physics</i> , <b>2010</b> , 108, 013110	2.5	17
196	Deep level transient spectroscopy signatures of majority traps in GaN p-n diodes grown by metal-organic vapor-phase epitaxy technique on GaN substrates. <i>Physica B: Condensed Matter</i> , <b>2009</b> , 404, 4889-4891	2.8	17
195	Carrier recombination and diffusion in GaN revealed by transient luminescence under one-photon and two-photon excitations. <i>Applied Physics Letters</i> , <b>2006</b> , 89, 172119	3.4	17
194	Optical gain in homoepitaxial GaN. <i>Applied Physics Letters</i> , <b>2004</b> , 85, 952-954	3.4	17
193	Nitride superluminescent diodes with broadened emission spectrum fabricated using laterally patterned substrate. <i>Optics Express</i> , <b>2016</b> , 24, 9673-82	3.3	17
192	Beyond Quantum Efficiency Limitations Originating from the Piezoelectric Polarization in Light-Emitting Devices. <i>ACS Photonics</i> , <b>2019</b> , 6, 1963-1971	6.3	16
191	Band gap engineering of In(Ga)N/GaN short period superlattices. <i>Scientific Reports</i> , <b>2017</b> , 7, 16055	4.9	16
190	Photoreflectance of InN and InN:Mg layers: An evidence of Fermi level shift toward the valence band upon Mg doping in InN. <i>Applied Physics Letters</i> , <b>2008</b> , 93, 131917	3.4	16
189	Resonant localized donor state above the conduction band minimum in InN. <i>Applied Physics Letters</i> , <b>2005</b> , 86, 262105	3.4	16
188	Metal-Insulator Transition in GaN Crystals. <i>Physica Status Solidi (B): Basic Research</i> , <b>1996</b> , 198, 223-233	1.3	16
187	Blue Laser on High N <sub>2</sub> Pressure-Grown Bulk GaN. <i>Acta Physica Polonica A</i> , <b>2001</b> , 100, 229-232	0.6	16
186	High pressure fabrication and processing of GaN:Mg. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , <b>1999</b> , 59, 1-5	3.1	15
185	Effect of Si Doping on the Structure of GaN. <i>Materials Research Society Symposia Proceedings</i> , <b>1996</b> , 423, 487		15
184	Hole carrier concentration and photoluminescence in magnesium doped InGaN and GaN grown on sapphire and GaN misoriented substrates. <i>Journal of Applied Physics</i> , <b>2010</b> , 108, 023516	2.5	14
183	Optically pumped GaN/AlGaIn separate-confinement heterostructure laser grown along the (112̄0) nonpolar direction. <i>Applied Physics Letters</i> , <b>2007</b> , 90, 081104	3.4	14
182	Bulk GaN crystals grown at high pressure as substrates for blue-laser technology. <i>Physica Status Solidi A</i> , <b>2003</b> , 200, 9-12		14
181	Study of dopant activation in bulk GaN:Mg. <i>Physica B: Condensed Matter</i> , <b>2001</b> , 308-310, 47-50	2.8	14



180	Different pressure coefficients of the light emission in cubic and hexagonal InGaN/GaN quantum wells. <i>Applied Physics Letters</i> , <b>2002</b> , 81, 232-234	3.4	14
179	Study of light emission from GaN/AlGaN quantum wells under power-dependent excitation. <i>Journal of Applied Physics</i> , <b>2002</b> , 91, 9622	2.5	14
178	Ultralow threshold powers for optical pumping of homoepitaxial InGaN/GaN/AlGaN lasers. <i>Applied Physics Letters</i> , <b>2002</b> , 81, 3735-3737	3.4	14
177	High pressure investigation of ferroelectric phase transition in PbSnTe. <i>Solid State Communications</i> , <b>1981</b> , 38, 59-62	1.6	14
176	High temperature phase transition in Pb <sub>5</sub> Ge <sub>3</sub> O <sub>11</sub> . <i>Physica Status Solidi A</i> , <b>1976</b> , 35, K165-K167		14
175	Universal behavior of photoluminescence in GaN-based quantum wells under hydrostatic pressure governed by built-in electric field. <i>Journal of Applied Physics</i> , <b>2012</b> , 112, 053509	2.5	13
174	Tailoring the light-matter coupling in anisotropic microcavities: Redistribution of oscillator strength in strained m-plane GaN/AlGaN quantum wells. <i>Physical Review B</i> , <b>2011</b> , 84,	3.3	13
173	In-clustering effects in InAlN and InGaN revealed by high pressure studies. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2010</b> , 207, 1369-1371	1.6	13
172	Band-to-band character of photoluminescence from InN and In-rich InGaN revealed by hydrostatic pressure studies. <i>Applied Physics Letters</i> , <b>2006</b> , 89, 121915	3.4	13
171	Photoconductive Z-scan measurement of multiphoton absorption in GaN. <i>Journal of Applied Physics</i> , <b>2002</b> , 92, 6930-6932	2.5	13
170	Infrared studies on GaN single crystals and homoepitaxial layers. <i>Journal of Crystal Growth</i> , <b>2000</b> , 218, 161-166	1.6	13
169	Band gaps in InN/GaN superlattices: Nonpolar and polar growth directions. <i>Journal of Applied Physics</i> , <b>2013</b> , 114, 223102	2.5	12
168	Secondary ions mass spectroscopy measurements of dopant impurities in highly stressed InGaN laser diodes. <i>Applied Physics Letters</i> , <b>2011</b> , 98, 241115	3.4	12
167	Mode dynamics of high power (InAl)GaN based laser diodes grown on bulk GaN substrate. <i>Journal of Applied Physics</i> , <b>2007</b> , 101, 083109	2.5	12
166	Energy gap in GaN bulk single crystal between 293 and 1237 K. <i>Journal of Crystal Growth</i> , <b>2002</b> , 235, 111-114	1.6	12
165	Structural and electronic properties of wurtzite MgZnO and BeMgZnO alloys and their thermodynamic stability. <i>Journal of Applied Physics</i> , <b>2016</b> , 120, 215704	2.5	12
164	Comparison of wurtzite GaN/AlN and ZnO/MgO short-period superlattices: Calculation of band gaps and built-in electric field. <i>Physica Status Solidi (B): Basic Research</i> , <b>2017</b> , 254, 1600704	1.3	11
163	InGaN laser diodes with reduced AlGaN cladding thickness fabricated on GaN plasmonic substrate. <i>Applied Physics Letters</i> , <b>2013</b> , 102, 151102	3.4	11

162	Influence of substrate misorientation on properties of InGaN layers grown on freestanding GaN. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2008</b> , 5, 1485-1487		11
161	Blue-Laser Structures Grown on Bulk GaN Crystals. <i>Physica Status Solidi A</i> , <b>2002</b> , 192, 320-324		11
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159	Pressure induced phase transition in PbSnTe. <i>Solid State Communications</i> , <b>1979</b> , 30, 77-80	1.6	11
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